Features

- SiC MOSFET Technology
- High Speed Switching
- Reduction Of Heat Sink Requirements
- Essentially No Switching Losses
- Halogen Free. “Green” Device (Note 1)
- Lead Free Finish/RoHS Compliant("P" Suffix Designates RoHS Compliant. See Ordering Information) (Note2)

SiC N-CHANNEL MOSFET

Maximum Ratings

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance Junction to Ambient,Max(Note 3): 62°C/W
- Thermal Resistance Junction to Case,Typ : 0.4°C/W

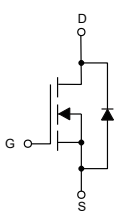
Applications

- Solar Inverters
- Uninterruptible Power Supply
- Photovoltaic Inverter
- Battery Chargers
- Motor Drives

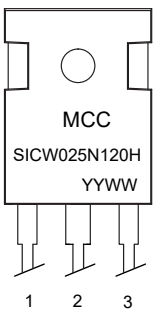
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	1200	V
Gate-Source Voltage(Note 4)		V_{GSmax}	-10/+25	V
Gate-Source Voltage		V_{GSop}	-5/+20	V
Continuous Drain Current V_{GS}=20V	Tc=25°C	I_D	86	A
	Tc=110°C		56	
Pulsed Drain Current (Note 5)		I_{DM}	327	A
Total Power Dissipation	Tc=25°C	P_D	375	W
	Tc=110°C		162	
Avalanche Energy, Single Pulse	V_{DD}=100V, I_D=14A	E_{AS}	3.0	J

Note1:Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
Note2:High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.
Note3:Device in a still air environment with TA=25°C.
Note4:AC f > 1Hz, duty cycle < 1%
Note5:Pulse Test: Pulse Width Limited by Tjmax.

Internal Structure and Marking Code

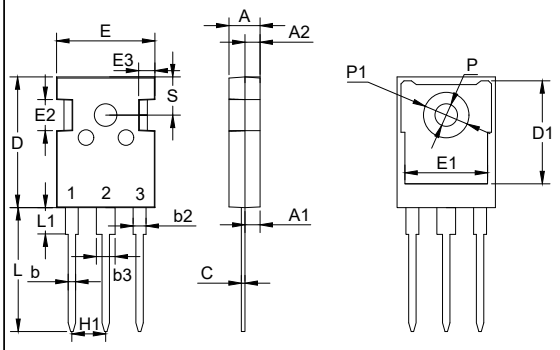


1. Gate
2. Drain
3. Source



Device Code: SICW025N120H
Date Code: YYWW (Year & Week)

TO-247AB



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.087	0.103	2.21	2.61	
A2	0.073	0.085	1.85	2.15	
b	0.039	0.055	1.00	1.40	
b2	0.075	0.087	1.91	2.21	
C	0.020	0.028	0.50	0.70	
D	0.815	0.839	20.70	21.30	
D1	0.640	0.663	16.25	16.85	
E	0.610	0.634	15.50	16.10	
E1	0.512	0.535	13.00	13.60	
E2	0.189	0.205	4.80	5.20	
E3	0.091	0.106	2.30	2.70	
L	0.772	0.796	19.62	20.22	
L1	-	0.177	-	4.50	
P	0.134	0.150	3.40	3.80	Φ
P1		0.287	-	7.30	Φ
S	0.242		6.15		TYP
H1	0.214		5.44		TYP
b3	0.110	0.126	2.80	3.20	

Electrical Characteristics @ T_j=25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=100μA	1200			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =20V			250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=1200V, V_{GS}=0V			50	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=50mA	2	3.0	4.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=20V, I_D=40A		25	33	mΩ
		V_{GS}=20V, I_D=40A,T_j =175°C		45		mΩ
Internal Gate Resistance	R_g	f=1MHz, V_{AC}=25mV		0.6		Ω
Transconductance	g_{FS}	V_{DS}=15V, I_D=40A		18.6		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=800V,V_{GS}=0V, f=1MHz,V_{AC}=25mV		4909		pF
Output Capacitance	C_{oss}			198		
Reverse Transfer Capacitance	C_{rss}			34		
Coss Stored Energy	E_{oss}			80		μJ
Total Gate Charge	Q_g	V_{DS}=800V,V_{GS}=-5/+20V, I_D=40A		305		nC
Gate-Source Charge	Q_{gs}			91		
Gate-Drain Charge	Q_{gd}			88		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=800V, V_{GS}=-4/+20V, R_G=2.7Ω, I_D=40A, R_L=20Ω		31		ns
Rise Time	t_r			55		
Turn-Off Delay Time	$t_{d(off)}$			8		
Fall Time	t_f			12		
Turn-On switching energy	E_{on}	V_{DD}=800V, V_{GS}=0/+20V, R_G=2.7Ω, I_D=40A		200		μJ
Turn-Off switching energy	E_{off}			305		
Diode Characteristics						
Continuous Body Diode Current	I_S	V_{GS}=0V, T_C=25°C		60		A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_{SD}=12A		3		V
Reverse Recovery Time	t_{rr}	V_{GS}=0V, I_{SD}=30A, V_{DS}=400V, dI_F/dt=300A/μs		79		ns
Reverse Recovery Charge	Q_{rr}			340		nC
Peak Reverse Recovery Current	I_{rrm}			8.2		A

Curve Characteristics(T_J=25℃ unless otherwise specified)

Fig. 1 - Typical Output Characteristic (T_j=25°C)

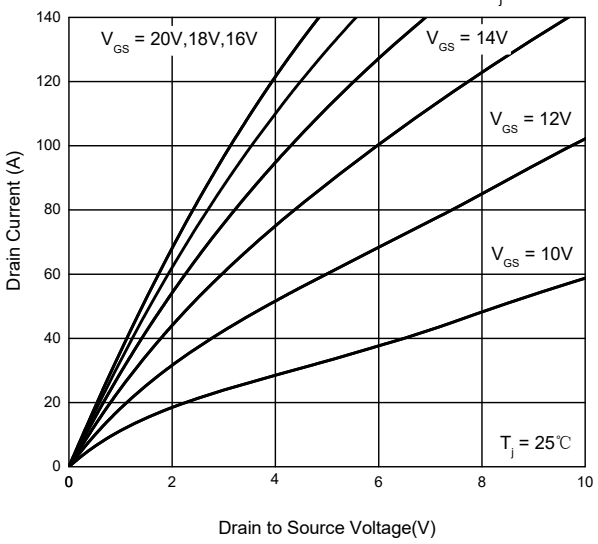


Fig. 2 - Typical Output Characteristic (T_j=175°C)

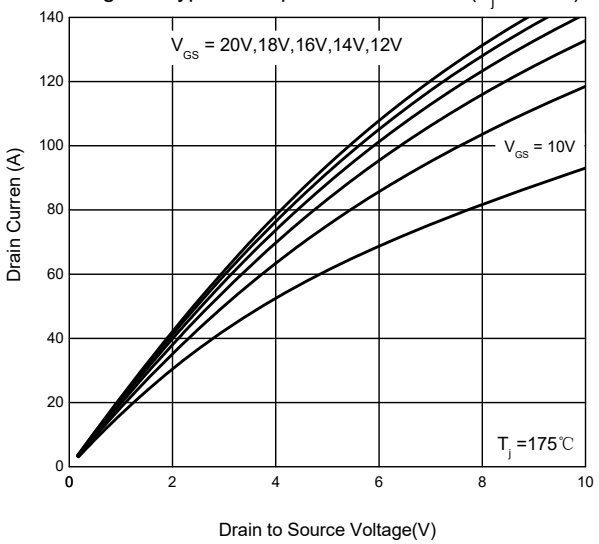


Fig. 3 -On-Resistance vs. Drain Current

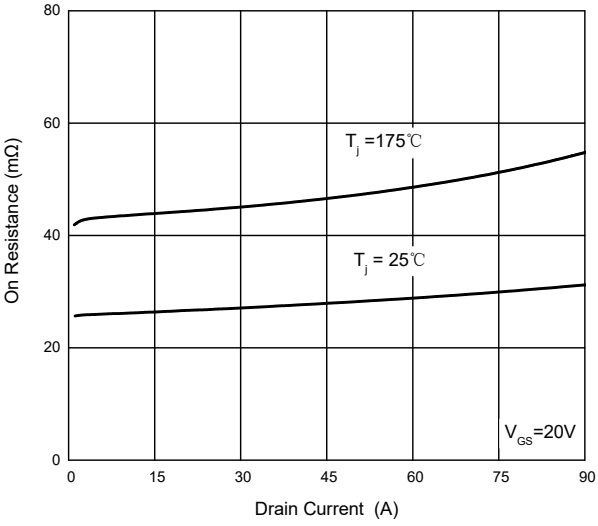


Fig. 4 - Typical Transfer Characteristic

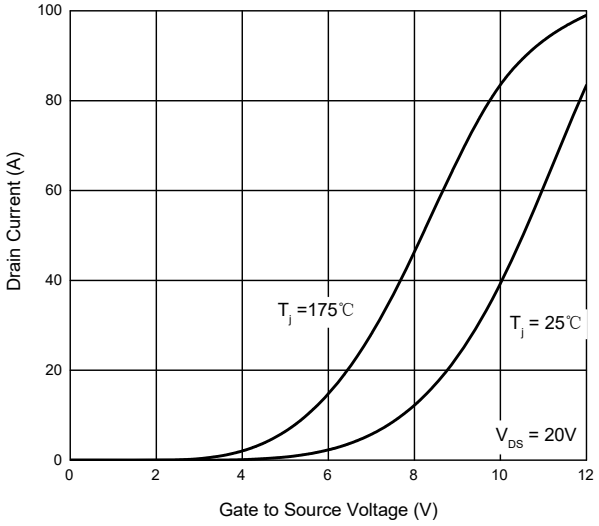


Fig. 5 - On-Resistance vs. Gate Voltage

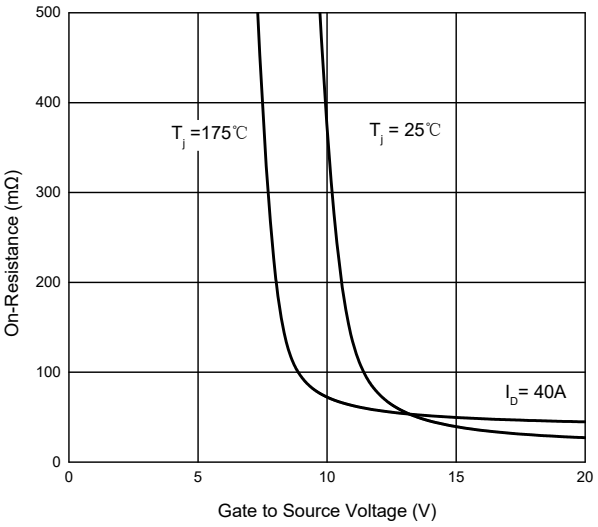
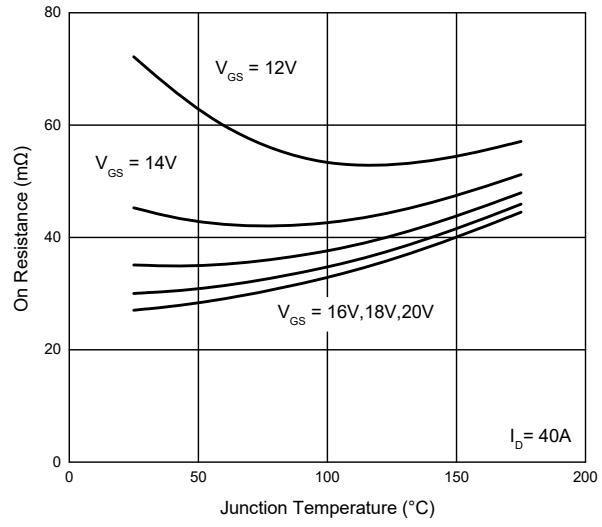


Fig. 6 - On-Resistance vs. Temperature



Curve Characteristics(T_J=25℃ unless otherwise specified)

Fig. 7 - Normalized On-Resistance vs. Temperature

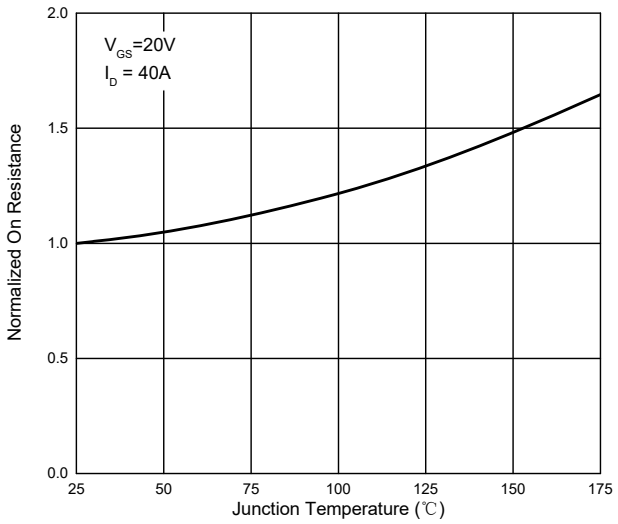


Fig. 8 - Reverse Output Voltage

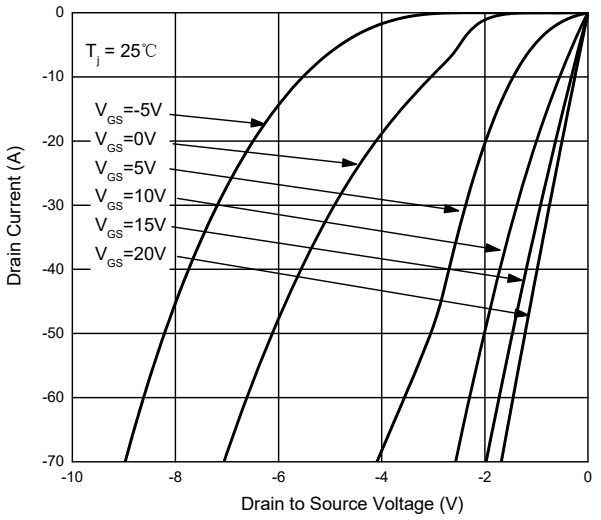


Fig. 9 - Reverse Output Voltage

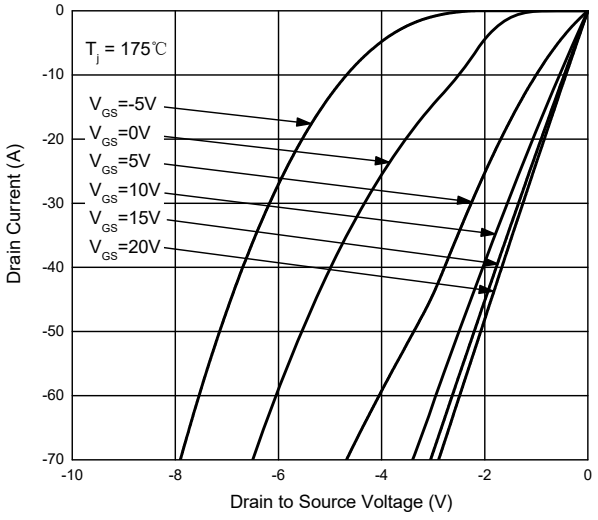


Fig. 10 - Capacitances vs. V_{DS}

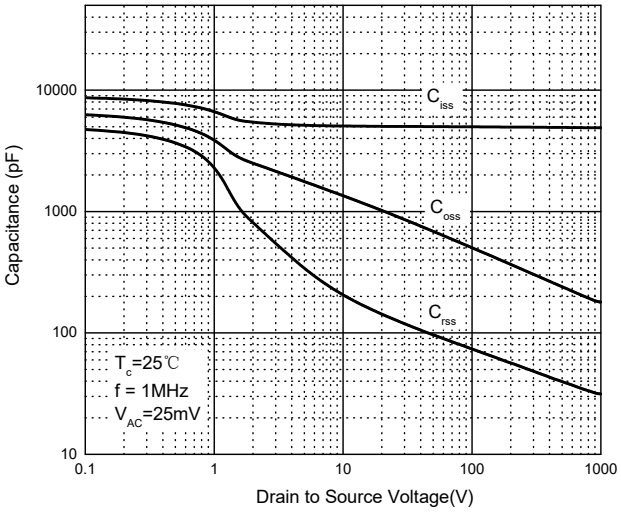


Fig. 11 - Threshold Voltage vs. Temperature

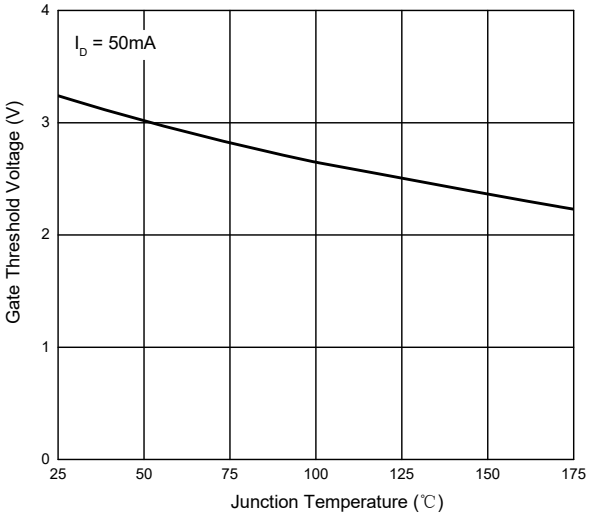
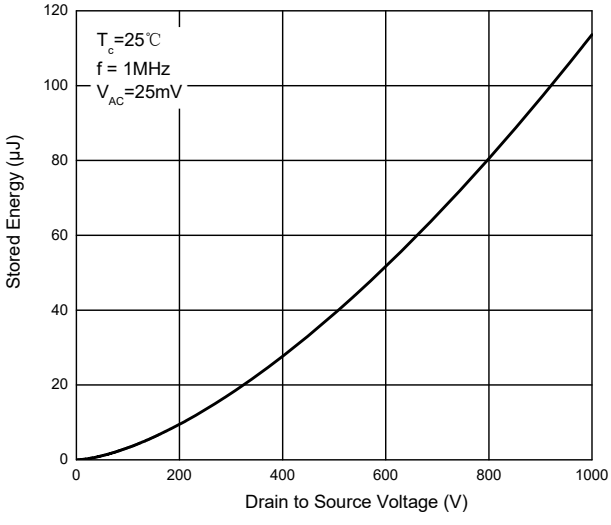


Fig. 12 - Output Capacitor Stored Energy



Curve Characteristics(T_J=25℃ unless otherwise specified)

Fig. 13 - Power Derating

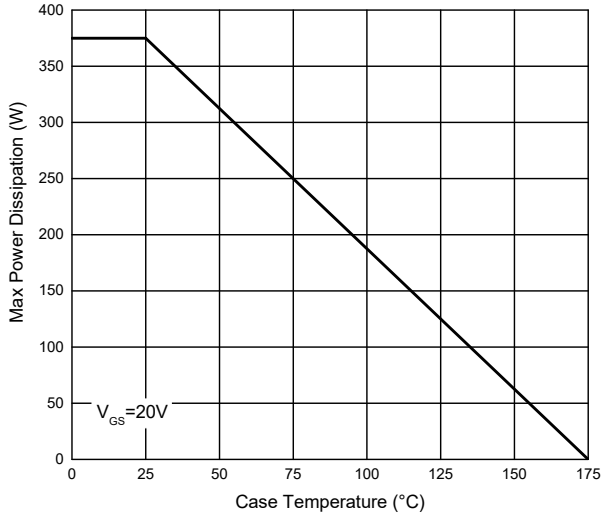


Fig. 14 - Drain Current Derating

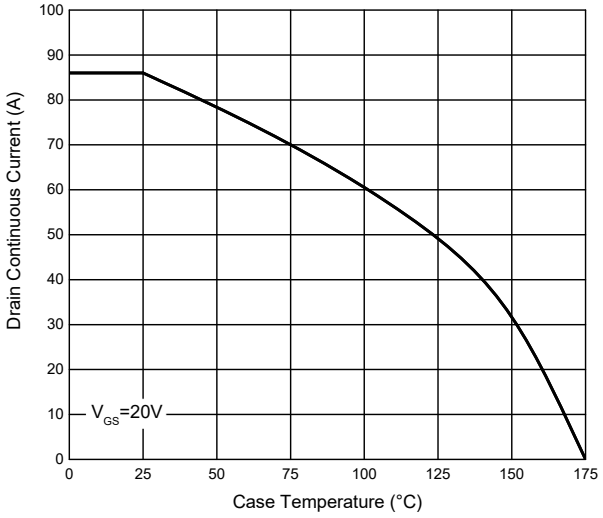


Fig. 15 -Safe Operation Area

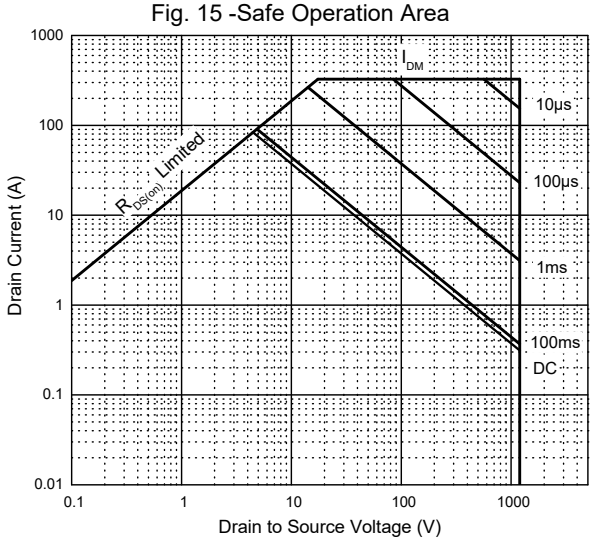


Fig. 16 - Typical Gate Charge

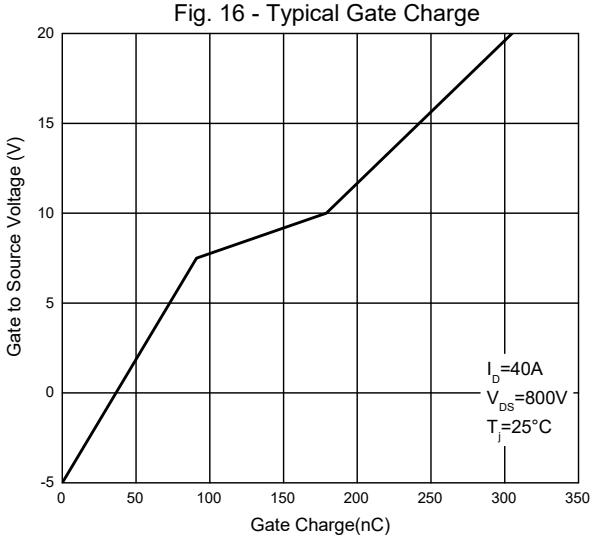


Fig. 17 - Clamped Inductive Switching Energy vs. Drain Current

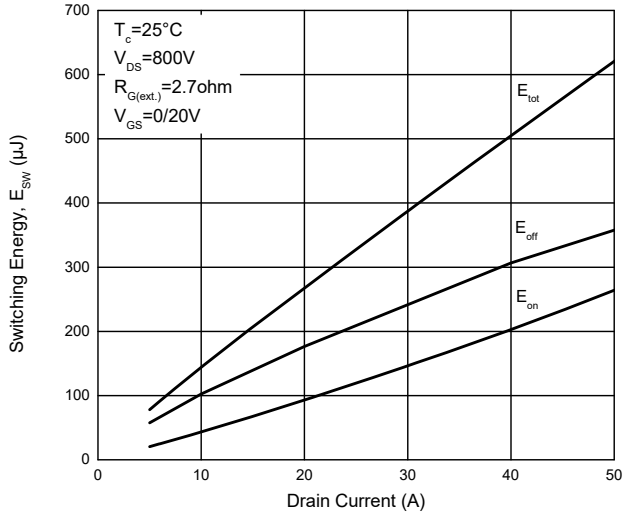
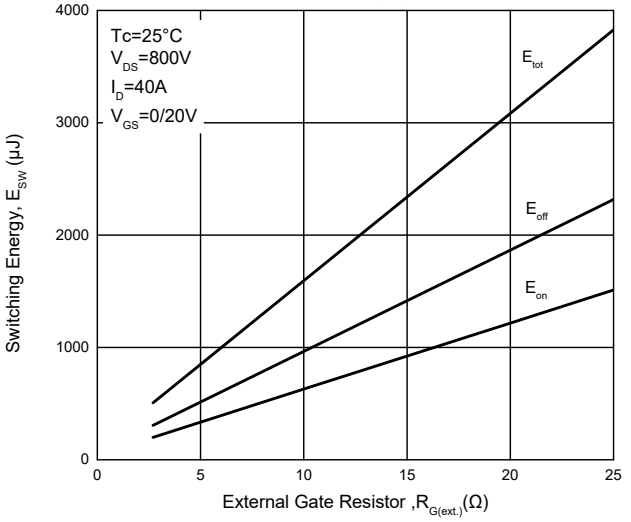
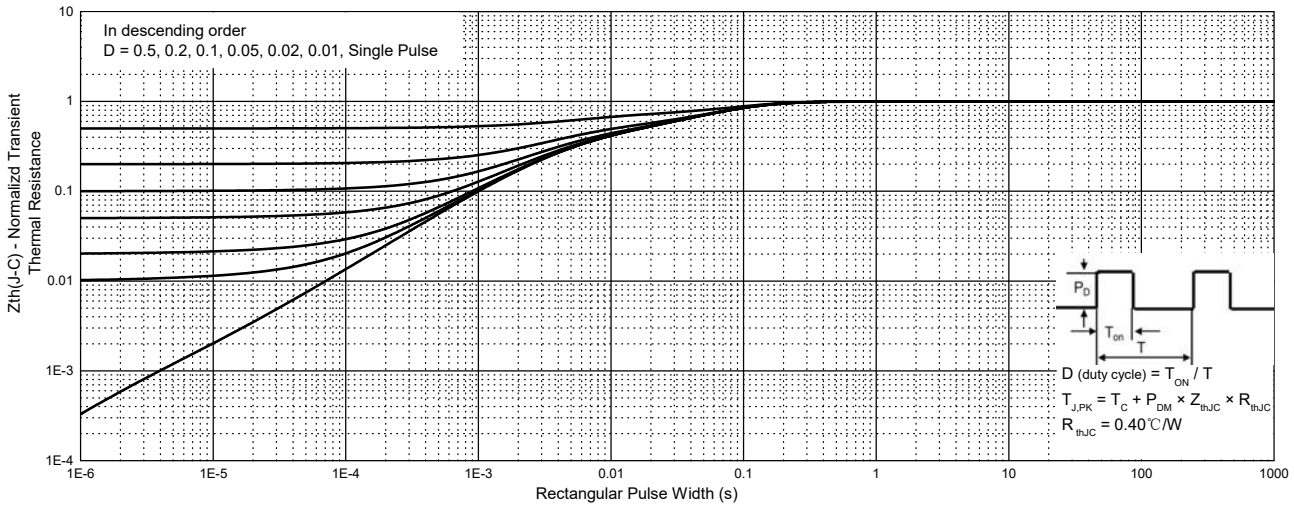


Fig. 18 - Clamped Inductive Switching Energy vs. External Gate Resistor ($R_{G(ext.)}$)



Curve Characteristics(T_J=25℃ unless otherwise specified)

Fig.19 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
SICW025N120H-BP	Tube:30pcs/Tube, 1.8K/Ctn;